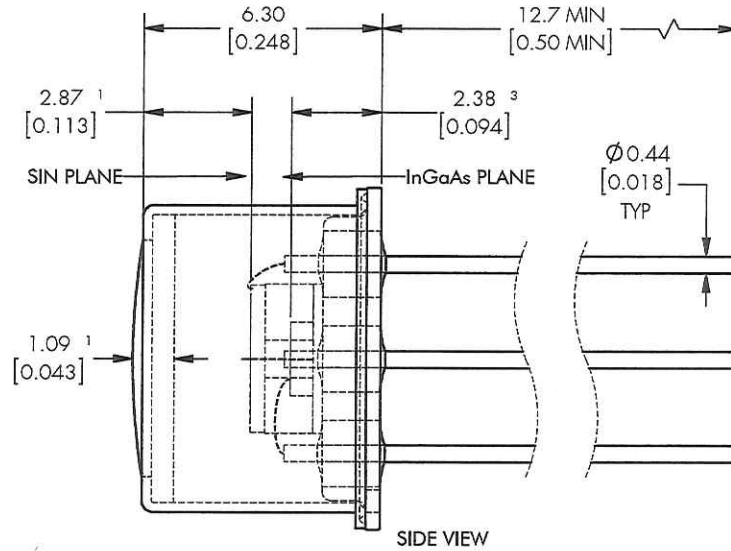
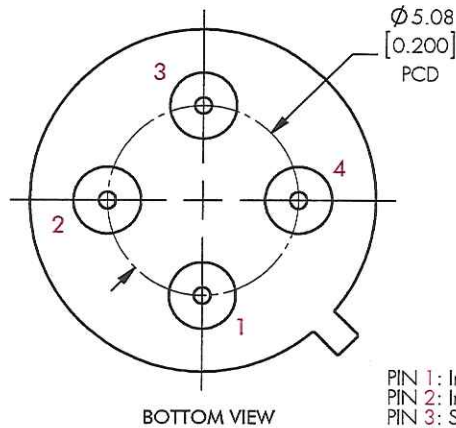


Note:  
Active area concentric to  
Datum A within 50µm.

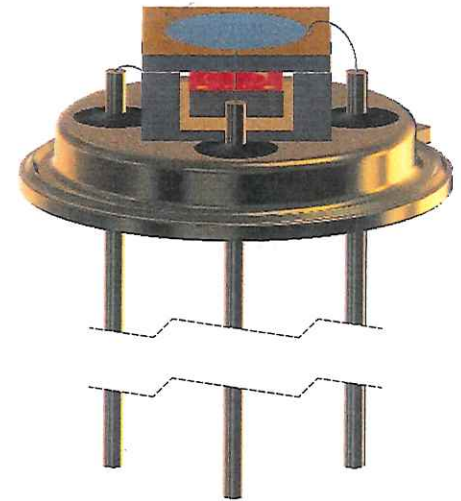
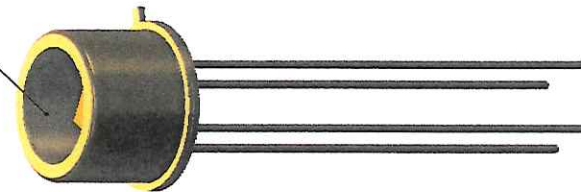


- <sup>1</sup> Distance from top of SIN active area to top of device.
- <sup>2</sup> Window thickness.
- <sup>3</sup> Distance from top of InGaAs active area to bottom of device.



PIN 1: InGaAs Anode  
PIN 2: InGaAs Cathode  
PIN 3: Si Anode  
PIN 4: Si Cathode

BK7 Window



Drawn By: *David*  
On: 9/19/2017  
Drafting: *David*  
Engineering: *Andrew*  
Production: *Beard*  
Management: *William*



PROPRIETARY AND CONFIDENTIAL  
THE INFORMATION CONTAINED IN  
THIS DRAWING IS THE SOLE PROPERTY  
OF LASER COMPONENTS. ANY  
REPRODUCTION IN PART OR AS A  
WHOLE WITHOUT THE WRITTEN  
PERMISSION OF LASER COMPONENTS  
IS PROHIBITED.

UNLESS OTHERWISE SPECIFIED:  
DIMENSIONS ARE IN MM (IN)  
STANDARD TOLERANCES - MM:  
ANGULAR: ±3°  
ONE PLACE DECIMAL: ±0.5  
TWO PLACE DECIMAL: ±0.1

TITLE:  
4-Pin TO-39 IG/SIN Package  
ø3mm SIN, 1.3mm InGaAs Active Area  
Silicon & InGaAs PIN  
Product Outline Drawing

REV.	DESCRIPTION	DATE	REVISED BY
REVISION			

SIZE	DWG. NO.	REV
B	BICIG17X1.3SIN3.09M	
SCALE: 1:0.04		SHEET 1 OF 1